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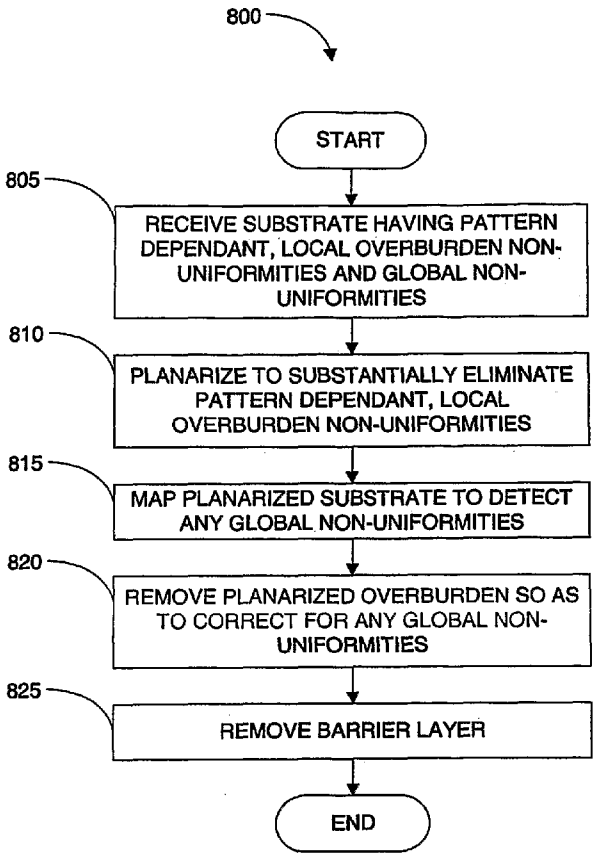
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[Continued on next page]

(54) Title: SYSTEM, METHOD AND APPARATUS FOR IMPROVED LOCAL DUAL-DAMASCENE PLANARIZATION



(57) Abstract: A system and method for planarizing a patterned semiconductor substrate includes receiving a patterned semiconductor substrate. The patterned semiconductor substrate having a conductive interconnect material filling multiple of features in the pattern. The conductive interconnect material having an overburden portion. The overburden portion includes a localized non-uniformity. An additional layer is formed an the overburden portion. The additional layer and the overburden portion are planarized. The planarizing process substantially entirely removes the additional layer.

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